

| L Number | Hits | S arch Text | DB | Time stamp |
|----------|------|---|---|---------------------|
| 1 | 5583 | (gat adj l ctr de) and ((titanium adj nitride) or TiN) and sili id | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/06/02 15:12 |
| 2 | 332 | (gate adj electrode) and ((titanium adj nitride) or TiN) and silicide and ((fig or fig. or figure) near10 electrode) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/06/02 15:13 |
| 3 | 246 | (gate adj electrode) and ((titanium adj nitride) or TiN) and silicide and ((fig or fig. or figure) near10 electrode) and (method or process).ti,ab,clm. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/06/02 15:13 |
| 4 | 52 | (gate adj electrode) and ((titanium adj nitride) or TiN) and silicide and ((fig or fig. or figure) near10 electrode) and (method or process).ti,ab,clm. and (barrier adj layer) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/06/02 15:14 |
| 5 | 12 | (gate adj electrode) and ((titanium adj nitride) or TiN) and silicide and ((fig or fig. or figure) near10 electrode) and (method or process).ti,ab,clm. and (barrier adj layer) and (tin or (titanium near nitride)).ti,ab,clm. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/06/02 15:15 |
| 6 | 499 | (gate adj electrode) and ((titanium adj nitride) or TiN) and silicide and (method or process).ti,ab,clm. and (barrier adj layer) and (tin or (titanium near nitride)).ti,ab,clm. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/06/02 15:15 |
| 7 | 183 | (gate adj electrode).ti,ab,clm. and ((titanium adj nitride) or TiN) and silicide and (method or process).ti,ab,clm. and (barrier adj layer) and (tin or (titanium near nitride)).ti,ab,clm. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/06/02 15:16 |
| 8 | 111 | (gate adj electrode).ti,ab,clm. and ((titanium adj nitride) or TiN) and silicide and (method or process).ti,ab,clm. and (barrier adj layer).ti,ab,clm. and (tin or (titanium near nitride)).ti,ab,clm. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/06/02 15:16 |
| 9 | 110 | (gate adj electrode).ti,ab,clm. and ((titanium adj nitride) or TiN).ti,ab,clm. and silicide and (method or process).ti,ab,clm. and (barrier adj layer).ti,ab,clm. and (tin or (titanium near nitride)).ti,ab,clm. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/06/02 15:16 |
| 10 | 76 | (gate adj lectrod).ti,ab,clm. and ((titanium adj nitride) or TiN).ti,ab,clm. and silicide.ti,ab,clm. and (m thod or process).ti,ab,clm. and (barri r adj layer).ti,ab, lm. and (tin r (titanium near nitrid)),ti,ab,clm. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/06/02 15:17 |

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| 11 | 86 | (gat adj lectr de).ti,ab,clm. and ((titanium adj nitrid) or TiN).ti,ab,clm. and silicide.ti,ab,clm. and (meth d or pr c ss).ti,ab,clm. and (barri r near2 layer).ti,ab, lm. and (tin r (titanium n ar nitride)).ti,ab,clm. | USPAT; US-P PUB; EPO; JPO; DERWENT; IBM_TDB | 2004/06/02 15:17 |
| 12 | 19 | (gate adj electrode).ti,ab,clm. and ((titanium adj nitride) or TiN).ti,ab,clm. and silicide.ti,ab,clm. and (method or process).ti,ab,clm. and (barrier near2 layer).ti,ab,clm. and (tin or (titanium near nitride)).ti,ab,clm. and (electrode same (film or layer) same barrier same ((titanium near nitride) or tin)).ti,ab,clm. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/06/02 15:20 |
| 13 | 0 | 09/9922804 | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/06/02 15:20 |
| 14 | 1 | 09/922804 | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/06/02 15:22 |
| 15 | 4374 | (titanium near silicide) near5 (form or forming or formed) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/06/02 15:23 |
| 16 | 1255 | electrode.clm. and (titanium near silicide) near5 (form or forming or formed) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/06/02 15:23 |
| 17 | 207 | electrode.clm. and ((titanium near silicide) near5 (form or forming or formed)) and (titanium adj nitride).clm. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/06/02 15:23 |
| 18 | 61 | electrode.clm. and ((titanium near silicide) near5 (form or forming or formed)) and (titanium adj nitride).clm. and barrier.clm. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/06/02 15:23 |
| 19 | 40 | electrode.clm. and ((titanium near silicide) near5 (form or forming or formed)) and ((titanium adj nitride) near10 barrier).clm. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/06/02 15:24 |

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| 20 | 1 | ele trod .clm. and ((titanium n ar silicid) near5 no near5 (f rm r f rming r f rm d)) and ((titanium adj nitrid) near10 barrier).clm. | USPAT; US-PGPUB; EPO; JP ; DERWENT; IBM_TDB | 2004/06/02 15:24 |
| 21 | 40 | electr de.clm. and ((titanium near silicide) near5 (form or forming or formed)) and ((titanium adj nitride) near10 barrier).clm. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/06/02 15:25 |
| 22 | 0 | (electrode.clm. and ((titanium near silicide) near5 (form or forming or formed)) and ((titanium adj nitride) near10 barrier).clm.) not silicide | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/06/02 15:25 |
| 23 | 742 | ((titanium adj nitride) near5 barrier).clm. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/06/02 15:25 |
| 24 | 85 | ((titanium adj nitride) near5 barrier).clm. and (gate adj electrode).clm. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/06/02 15:25 |
| 25 | 32 | ((titanium adj nitride) near5 barrier).clm. and (gate adj electrode).clm.) not silicide | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/06/02 15:26 |
| 26 | 1 | ((titanium adj nitride) near5 barrier).clm. and (gate adj electrode).clm.) not silicide and (electrode same (silicon or polysilicon) same (titanium adj nitride)).clm. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/06/02 15:28 |
| 27 | 160 | (electrode same (silicon or polysilicon) same (titanium adj nitride)).clm. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/06/02 15:28 |
| 28 | 576 | (electrode same (silicon or polysilicon) same (titanium adj nitride)).ti,ab,clm. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/06/02 15:28 |
| 29 | 323 | ((electrode same (silicon or polysilicon) same (titanium adj nitride)).ti,ab,clm.) not silicid | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/06/02 15:28 |

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| 30 | 91 | (((electrod same (silicon r p lysilicon) same (titanium adj nitride)).ti,ab, lm.) n t silicid) and (ann al r ann aled r ann aling or tr at or treating r treated or tr atment or cure or cur d or uring) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/06/02 15:29 |
| 31 | 66 | (((el ctrode sam (ilic n r polysilic n) same (titanium adj nitride)).ti,ab,clm.) not silicide) and (anneal or annealed or annealing or treat or treating or treated or treatment or cure or cured or curing).ti,ab,clm. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/06/02 15:29 |
| 33 | 20 | (((electrode same (silicon or polysilicon) same (titanium adj nitride)).ti,ab,clm.) not silicide) and (anneal or annealed or annealing or treat or treating or treated or treatment or cure or cured or curing).ti,ab,clm. and temperature.ti,ab,clm. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/06/02 15:33 |
| 34 | 10 | (method or process) same electrode same (silicon or polysilicon or poly-silicon) same (barrier near5 (titanium adj nitride)).ti,ab,clm. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/06/02 15:54 |
| 35 | 643 | (electrode near20 polysilicon near20 (barrier near2 layer)) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/06/02 15:55 |
| 36 | 65 | (electrode near20 polysilicon near20 (barrier near2 layer)).clm. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/06/02 15:55 |
| 37 | 11 | (electrode near20 polysilicon near20 (barrier near2 layer)).clm. and ((barrier near2 layer) near20 (titanium near nitride)).clm. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/06/02 15:58 |
| 38 | 3 | ((electrode near20 polysilicon near20 (barrier near2 layer)).clm. and ((barrier near2 layer) near20 (titanium near nitride)).clm.) not silicide | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/06/02 16:01 |
| 39 | 2 | (((electrode near20 polysilicon near20 (barrier near2 layer)).clm. and ((barrier near2 layer) near20 (titanium near nitride)).clm.) not silicide) and (anneal or annealing or annealed) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/06/02 16:02 |

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| 40 | 2 | ((lectrode near20 polysilic n near20 (barrier n ar2 lay r)).clm. and ((barrier n ar2 lay r) n ar20 (titanium near nitride)).clm.) n t silicide) and (anneal or ann aling or anneal d r treat or treating or tr ated or treatment) | USPAT; US-P PUB; EPO; JPO; DERWENT; IBM_TDB | 2004/06/02 16:02 |
| 41 | 2 | ((electrode near20 polysilicon near20 (barrier near2 layer)).clm. and ((barrier near2 layer) near20 (titanium near nitride)).clm.) not silicide) and (heat or heated or heating or anneal or annealing or annealed or treat or treating or treated or treatment) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/06/02 16:03 |